## On the Charge Ordering Observed by Recent STM Experiments

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W e present a perspective on the recent discoveries of possible charge ordering in underdoped  $B_{12}Sr_2CaCu_2O_{8+}$  and  $Na_xCa_2_xCuO_2Cl_2$  by high-resolution scanning tunnelling spectroscopy.

In an STM study of optim ally doped (B i2212) at B i<sub>2</sub>S r<sub>2</sub>C aC u<sub>2</sub>O 8+ nite applied magnetic eld, Ho man et al discovered that in the vicinity of vortex cores the STM tunnelling conductance exhibits a checkerboard spatial dependence [1], with Fourier peaks at Q = (2 = ;0); (0; 2 = ) and 4:3a (a is the lattice constant of the copper oxide plane). Subsequently Howald et al studied optimally doped B i2212 below T<sub>c</sub> at zero eld, and reported observation of a nondispersive, directionally asymmetric tunneling conductance with Fourier peaks at Q = (2 = ;0); (0; 2 = ) and 4a for low energies ( $\sqrt[1]{j} < 25 \text{m eV}$ ) [2]. However this result was not con m ed by later experim ents [3[5]. In Ref.[3]5] high resolution STM studies of near-optim ally doped B i2212 below T<sub>c</sub> revealed rich bias-dependent quasiperiodic modulations of the STM tunnelling conductance. This phenomenon was explained as the quantum interference of quasiparticle de Broglie w aves [3, 4, 6]. R ef. [7]em phasized the deviation in the dispersion of the Fourier peaks in the (1;0) and (0;1) crystallographic directions from the simplest quasiparticle interference predictions.

In Ref.5] Vershin in et al have also reported results for  $T > T_c$ . Interestingly, at low energies they observed bias-independent conductance m odulations with Fourier peaks at Q = (2 = ;0); (0; 2 = ) and 4:7a[5].

Two very recent low temperature STM experiments on underdoped Bi2212[8] and N a\_x C a\_2  $_x$  C uO  $_2$  C l\_2 (N aCCOC) [9] reported bias independent quasiperiodic m odulations of the local conductance over a wide range of energy. These modulations have Fourier peaks at Q = (2 = ;0); (0; 2 = ), w ith4:5a for B i2212, 4a for N aCCOC. Inspection of the real space and m odulation patterns shows that they are in phase upon bias reversal[5, 8, 9]. Ref.[10] and Ref.[11] suggest that this bias symmetry contains vital information about the origin of these phenom ena. Here we would like to point out that this sym m etry could appear sim ply because the system is a doped M ott insulator. Indeed, doping a M ott insulator quite comm only transfers spectral weight (for both electrons and holes) proportional to the doping density from above the charge gap to low energy. As a result, when the doping density modulates in space, both the electron and hole spectral functions modulate with the sam e phase.

Despite the similarities between the phenomena re-



FIG.1: a) Caricature of the observed spatial modulation in dI=dV in Ref.[9]. b) Spatially averaged spectral function of the hole crystal. The spectral peaks marked by arrows correspond to states whose wavefunction is peaked at the solitons.

ported in Ref.[9] and Ref.[9], the B i2212 and N aCCOC results are di erent in three in portant aspects. 1) The charge period for B i2212 is not an integral multiple of the underlying lattice constant, while that of N aCCOC is. 2) For B i2212 the 4.5a m odulation appears in dI=dV spectrum only when jV j = 65m V, while in N aCCOC the signal appears right from zero bias. 3) For jV j = 30m V B i2212 exhibits bias-dependent quasiparticle interference m odulation [3], while such a signal is di cult to discern in N aCCOC. Due to these di erences it is possible that the phenom enon observed in N aCCOC is due to true charge order, while that observed in B i2212 is due to a yet-uncondensed charge order [8, 9].

The above STM experiments constitute an important set of observations concerning the electronic structure of the cuprates. The purpose of this paper is to present our interpretation of the results in Ref.[1, 5, 8, 9].

For N aCCOC, the dI=dV m odulation patterns consist of clearly visible 4 4 unit cells over a wide range of bias voltages [9] (150mVV V 150mV). A caricature of the real space pattern seen in Ref.[9] is shown in Fig.1a, where bright/dark marks regions of high/low di erential conductance. In Ref.[9] it is proposed that this spatial structure is due to the form ation of a W igner crystal of doped holes. In the following we corroborate this proposal with a theoretical analysis.

We start from a very underdoped situation where x = 1=16. This is the ideal doping density for a 4 4 unit cellhole crystal[12]. We interpret the bright region in each unit cell as having a high hole density (from a single hole delocalized in that region), and the dark re-

gion as having a low hole density. In the literature it has been proposed that doping a M ott insulator creates solitons (or spin bags/com posite quasiparticles) [13{15]. W e believe that the above bright and dark regions reveal the internal structure of each soliton. Recently Chen et al proposed that at commensurate doping densities a W igner crystalofhole pairs can form [16]. W e believe that due to C oulom b repulsion such a state is energetically unstable. M oreover, even with a strong short-ranged attractive interaction to overcom e the C oulom b interaction, w e would expect segregation into hole-rich and hole-poor regions rather than crystallization of hole pairs.

To demonstrate the possibility of a soliton crystal we perform a variational study of the usual Hubbard model with Coulomb and nearest neighbor exchange interactions added [17],

The variational ansatz we use is the most general Slater determ inant which allows spatially inhom ogeneous charge density, spin density, bond-current density, and superconducting pairing. Technically this is equivalent to factorizing the four-ferm ion terms in Eq. (1) into all possible quadratic com binations, and then solving the resulting quadratic H am iltonian self-consistently. The following results are obtained num erically for an 8 8 lattice with four holes and periodic boundary conditions.

It is quite encouraging that such a calculation does indeed yield a crystalline arrangement of the doped holes for a reasonable choice of parameters (t =  $0.3eV;U = 6eV;J = 0.3eV;V_c = 0.3eV$ , where  $V_c$  is the repulsion energy two holes experience at the nearest neighbor distance) [18]. We have checked that as long as the C oulom b interaction exists, the stability of the soliton crystal is not a ected by moderate modi cation of the above parameters. In all the cases we have studied the superconducting pairing and orbital current order are both absent when the holes crystallize. On the contrary we

nd that a non-zero antiferrom agnetic order coexists with the hole crystal.

In F ig.1b we show the spatially averaged spectral function. The spectral peaks m arked by arrows correspond to states whose wavefunctions are peaked at the soliton positions shown by the hole density (F ig.2a). The norm -squared wavefunctions of these states is released in the spatial variation of the local spectral function within

150m eV of the Ferm i level, as shown in Fig 2b. Although the detailed distribution of the spectral weight within the unit cell di ers for the positive and negative bias, the gross structure (i.e. the fact that the overall spectral weight peaks near the soliton) is the same. In that regard the spatial structure is sim ilar to that observed in Ref.[9]. Contrary to experiment, in our calculation the dark region basically has the LDOS spectrum



FIG. 2: a)Hole density distribution of the hole crystal. b)Spatialm odulation of the local spectral function. The images shown here are typical for 150 m eV E 150 m eV. A lthough the detailed distribution of the spectral weight within the unit cell di ers for the positive and negative bias, the gross structure (i.e. the fact that the overall spectral weight peaks near the soliton) is the sam e.

of the undoped insulator. We attribute the 150m eV peak in the dark region seen in Ref.[9] to the extra holes running on top of the W igner crystal background which are absent in our calculation.

We also note that when a soliton is produced on a Neel background, its location (on the A or B sublattice of the antiferrom agnetic order) depends on the spin of the rem oved electron. For example, if rem oving a spin up electron produces a soliton on the A sublattice, then rem oving a spin down electron will produce a soliton on the B sublattice. M oreover, our calculation shows that after rem oving an electron of a given spin, an electron of the opposite spin is always deeply bound to the soliton. This result is consistent with the notion that a soliton is a com posite particle of a charged void and a spin [14].

A weakness of the above variational study is that it underestim ates the quantum uctuation of spins. To study the internal structure of each soliton more carefully, we diagonalize the t-J model on a 4 4 plaquette with periodic boundary conditions. The H am iltonian we use for this study is

$$H = \sum_{\substack{\langle ij \rangle \\ \langle ij \rangle}}^{X} t P_{i} (c_{i}^{y} c_{j} + h c;) P_{j} + J (S_{i} S_{i} \frac{1}{4} n_{i} n_{j}); (2)$$

In the following we choose t = 0.3 eV, J = 0.1 eV. Motivated by the experimental indings we restrict the hole to a 3 3 plaquette in the unit cell. We compute the low-energy positive-bias[19] electron spectral function

A (x;!) =   
(! 
$$E^{0h} + E_0^{1h} + )j < {}^{0h}j_x^y j {}^{1h}_0 > j^2(3)$$

Here is the chem ical potential,  $j_{0}^{1h} > is the one-hole ground state with energy <math>E_{0}^{1h}$ , and  $j_{0}^{0h} > are the eigen$ states of the half-lled system, with energy E at most 2J above the half-lled ground state[20]. Fig.3 shows the hole density and A (x;!) at the three inequivalent sites of the central 3 3 plaquette. The hole density displays a similar spatial structure to that seen in the



FIG.3: Hole distribution and positive bias local spectral function. The center of each plaquette is a C u lattice site. The seven boundary sites of the 4 4 unit cell are replicated using periodic boundary conditions. The zero of the horizontal axis can be shifted by the chem ical potential (here = 0).

Hubbard model calculation. The tunnelling spectrum at the brightest site (i.e. site 3) exhibits two peaks. To understand these two peaks we note that in a 4 4 system the one-hole ground state is a spin doublet. The unpaired spin 1/2 is meant to m in ic the dangling spin in the soliton. A fter the tunnelling process the spin from the added electron can form a singlet or a triplet with the original soliton spin. The low er (higher) peak corresponds to the lowest energy spin doublet ! spin singlet (triplet) transitions. The peaks seen in Fig.3 are sim ilar to those observed in the bright region of the 4 4 unit cell in Ref.[9]. (Because we constrained the hole to the central 3 region, we cannot address the 150m eV peak ob-3 served in the dark region of the 4 4 unit cell.)

In the above discussions we have concentrated on doping density x = 1=16, where the system is a charge insulator. The actual doping density in the sam ple studied in Ref.[9] is likely to be higher [21]. We assert that when xdeviates from 1=16 the extra holes are delocalized on top of the W igner crystal background. These mobile holes m etallicize the system, and at low enough tem peratures such a metal can become a superconductor. W hen that happens the W igner crystalorder coexists with superconductivity. C learly an important question is the range of stability (in doping) of the W igner crystal. Currently we do not have an explicit answer to this question. However, we emphasize that in answering this question the e ects of lattice pinning (including the e ect of periodic potential as well as elastic lattice relaxation) are extremely important. We propose that the 4 4 unit cell Wigner crystalw ith extra m obile holes is adiabatically connected to the system with partially gapped Ferm i surface near the antinodes discussed later in this paper[22].

In the following we interpret the STM results for B i2212 [1, 3, 5, 8]. It is widely accepted that at optim al doping and lowest energies the only important elem entary excitations are nodal quasiparticles. (The phase uctuations are gapped due to the 3D C oulomb inter-



FIG. 4: The non-linear processes by which a quasiparticle is scattered by the Friedel oscillation set up by an impurity.

action.) As the excitation energy increases, antinodal quasiparticles and vortex-antivortex excitations join the list. The sm allest vortex-antivortex pair is a roton, which appears as a (damped) pole of the dynamic densitydensity correlation function. Because the signatures of charge ordering at wavevectors Q ( = ;0); (0; = )are observed in the underdoped regime, we assert that there exist four discrete roton minima at wavevectors (=;0); (0; =): These roton m in im a en-Q roton hance the DC charge susceptibility at Q  $_{\rm roton}$  . We believe that this enhancem ent is due to the particle-hole scattering across the nearly nested Ferm i surface in the antinodal region (with nesting wavevector Q nesting, see the left panel of F ig.4), so that  $Q_{roton}$ Q nesting .

D ue to this enhancement, Friedel-like modulations in the electron density at Q roton are induced by disorder. These modulations can in turn scatter the quasiparticles and give rise to enhanced quasiparticle interference modulations at wavevector Q roton. The lowest order such process is illustrated in Fig.4a [6, 7, 10, 23]. We believe that the bias-independent local conductance modulations in Ref.[1, 5] of optim ally doped B i2212 are due to the scattering described above.

In addition to Fig.4a the process depicted in Fig.4b can also scatter quasiparticles with momentum transfer Q<sub>nesting</sub>. This process is resonantly enhanced if the quasiparticle energy is greater than the excitation energy of the roton [24]. Given the fact that the 4.5a modulation phenomenon in Ref.[8] appears for j y j > 65m V, we think it quite likely it is due to the scattering process shown in Fig.4b. Finally, as pointed out by Zhou et al[25], the process shown in Fig.4c (without in purity involvement) can be very elective in destroying the coherence of antinodal quasiparticle excitations in ARPES studies [26].

As a function of decreasing x the roton m inim a deepen. W hen these m inim a touch zero, roton condensation occurs. This marks the onset of charge order. In an isotropic super uid such  $as^4H$  e the onset of crystallization coincides with the loss of super uidity. However,

in a system like the NaCCOC where the charge order is commensurate with the underlying crystalline lattice, interstitial/vacancy superconductivity can coexist with W igner crystal order due to lattice pinning e ects. In such a coexistence phase, the antinodal quasiparticles are strongly scattered by Q <sub>roton</sub> , hence a gap can open up in the antinodal region. How ever since Q roton does not connect the nodes the nodal quasiparticles can rem ain gapless if the potential from charge order is not too strong. Under these conditions the nodal quasiparticle peak can survive in the ARPES spectra [27]. Upon further decreasing x superconductivity eventually goes away. The loss of superconductivity is triggered by the Bose condensation of single vortices. W ith single vortices condensed all doped holes localize and the system becom es an insulator. A fter localization of holes the antiferrom agnetic order is presum ably restored. Because a real system has disorder, the W igner crystal order discussed above can only have nite-range correlations due to the Im ry-M a physics.

Is the charge ordering discussed here and in Ref.[5, 8, 9] responsible for the opening of the pseudogap? As has been pointed out in Ref.[8] this crucially depends the relation between the charge freezing (crossover) temperature  $T_{\rm charge}$  and the pseudogap temperature T . If  $T_{\rm charge}=T$  a strong argument can be made that the charge order actually drives the pseudogap formation. However, in our opinion it is likely that the pseudogap is caused by a di erent mechanism (e.g. spin singlet form mation), and  $T_{\rm charge} < T$ .

F inally, we note that like stripes[28], the hole crystal discussed in this paper represents yet another form of charge order. We do not have much to say about how the system chooses one form or the other. We hat is important is that the cuprates seem to have a tendency to form some type of charge order. We hether these charge orders have anything to do with pairing is entirely unclear to us.

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- $\ensuremath{\left[17\right]}$  W e add the exchange term because without it the variational study precludes superconducting pairing.
- [18] Our choice of J here is bigger than the widely accepted value J 0:1eV in t-J model studies. This is because in the Hubbard model double occupancy is allowed. The extra charge uctuation suppresses the elect of J.
- [19] W e focus on the positive bias because experim entally the local spectrum is basically featureless for negative bias.
- [20] To m ake the computation tractable, we rst diagonalize the central 3 3 plaquette and then hybridize its lowest energy states with the remaining spin sector of the 4 4 system. In the one-hole(half-lled) sector we hybridize eigenstates of the 3 3 plaquette which have energies within 1:3J (2:1J) of the ground state. For this reason, in Eq. (3) we only sum over eigenstates of the half-lled 4 4 lattice with energy  $E^{0h} < E_0^{0h} + 2J$ , where  $E_0^{0h}$ is the ground state energy of the half-lled 4 4 lattice. For ! + < 0:6, the spectral function is not a ected by changing the num ber of hybridized 3 3 plaquette states.
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